

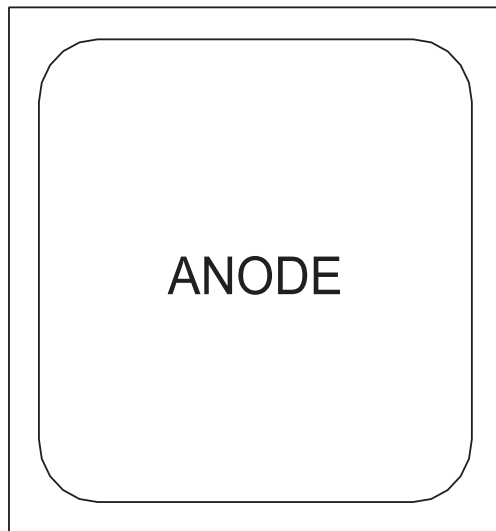
**PROCESS CPD06**  
**General Purpose Rectifier**  
3 Amp Glass Passivated Rectifier Chip



**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	89 x 89 MILS
Die Thickness	10.2 MILS
Anode Bonding Pad Area	66 x 66 MILS
Top Side Metalization	Ni/Au - 5,000Å/2,000Å
Back Side Metalization	Ni/Au - 5,000Å/2,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

**GROSS DIE PER 4 INCH WAFER**

1,490

**PRINCIPAL DEVICE TYPES**

1N5400 thru 1N5408

1N5550 thru 1N5554

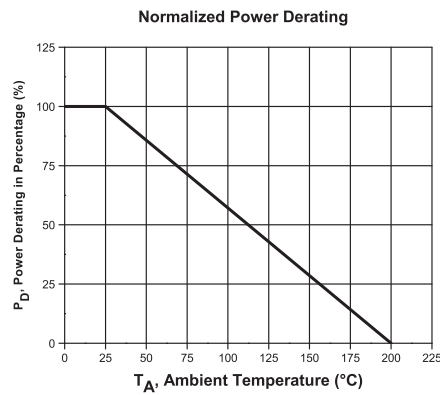
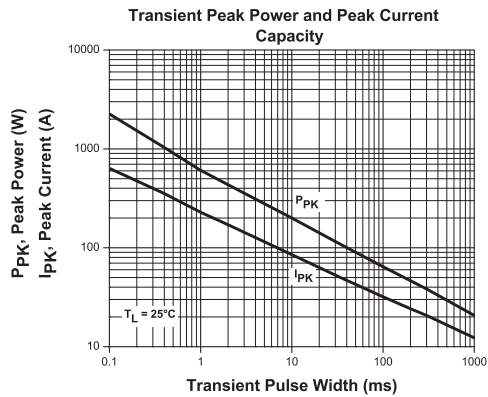
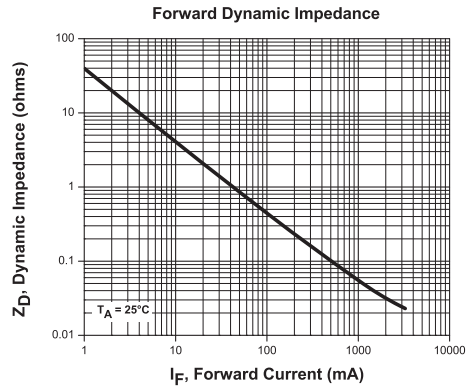
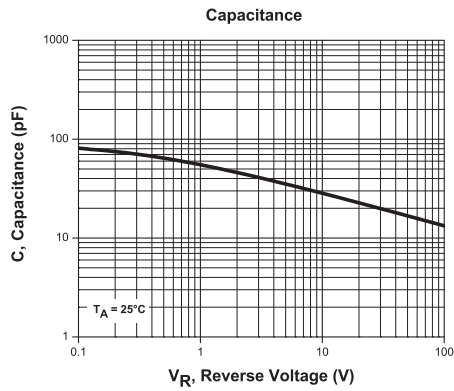
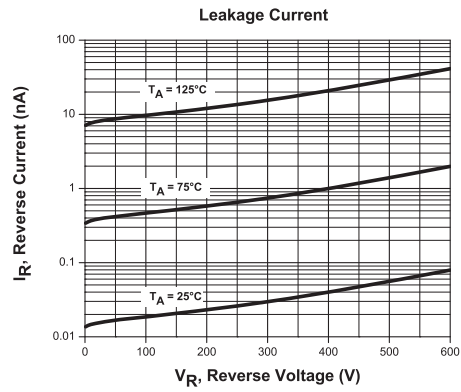
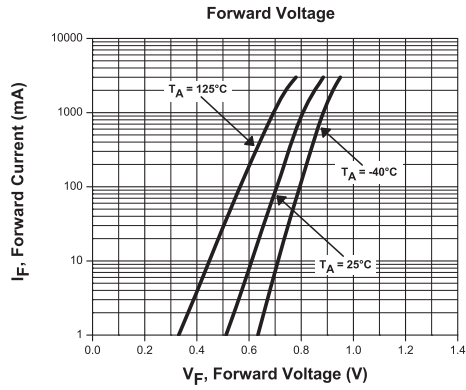
1N5624 thru 1N5627

CMR3-02 Series

R4 (22-March 2010)

# PROCESS CPD06

## Typical Electrical Characteristics



R4 (22-March 2010)